

IN THE CLAIMS:

Claims 1-5 have been amended herein. All of the pending claims 1 through 5 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A process for making a transistor comprising:  
providing a substrate;  
forming a dielectric layer on a portion of the substrate;  
forming a gate structure on-~~said~~ the dielectric layer having a gate oxide layer formed on-~~said~~ the dielectric layer and a metal silicide layer formed on-~~said~~ the gate oxide layer, ~~said~~ the gate structure having a first sidewall and a second sidewall, ~~said~~ the first sidewall and ~~said~~ the second sidewall defining therebetween within-~~said~~ the substrate a first contact region, a channel region and a second contact region; and  
forming first, second, and third subregions within-~~said~~ the second contact region, each subregion having a dopant concentration that differs from that of the other two subregions, ~~said~~  
forming of-~~said~~ the first, second, and third subregions comprising:  
depositing a conformal layer of dielectric material over-~~said~~ the substrate;  
anisotropically etching-~~said~~ the conformal layer of dielectric material, forming a layer of dielectric material on-~~said~~ the first sidewall and-~~said~~ the second sidewall;  
subjecting-~~said~~ the layer of dielectric material on-~~said~~ the first sidewall and-~~said~~ the second sidewall to an annealing/oxidation process;  
forming a single layer sidewall spacer overlying-~~said~~ the first sidewall and the second sidewall;  
introducing a first dopant into-~~said~~ the substrate to form-~~said~~ the first subregion;  
forming another single layer sidewall spacer overlying-~~said~~ the single layer sidewall spacer;  
introducing a second dopant into-~~said~~ the substrate to form-~~said~~ the second subregion;

substantially removing ~~said~~ the another single layer sidewall spacer; and  
introducing a third dopant into ~~said~~ the substrate to form ~~said~~ the third subregion.

2. (Currently Amended) The method of claim 1, wherein ~~said~~ the single layer sidewall spacer comprises a layer having a thickness in the range of between about 50 and 150 Angstroms.

3. (Currently Amended) The method of claim 1, wherein ~~said~~ the another single layer sidewall spacer comprises a layer of material having a thickness in the range of about 2 to 20 times a thickness of ~~said~~ the single layer sidewall spacer.

4. (Currently Amended) The method of claim 1, wherein ~~said~~ the another single layer sidewall spacer comprises a layer of material having a thickness of about 550 Angstroms.

5. (Currently Amended) The method of claim 1, wherein ~~said~~ the another single layer sidewall spacer comprises a material of one of silicon nitride and silicon dioxide.